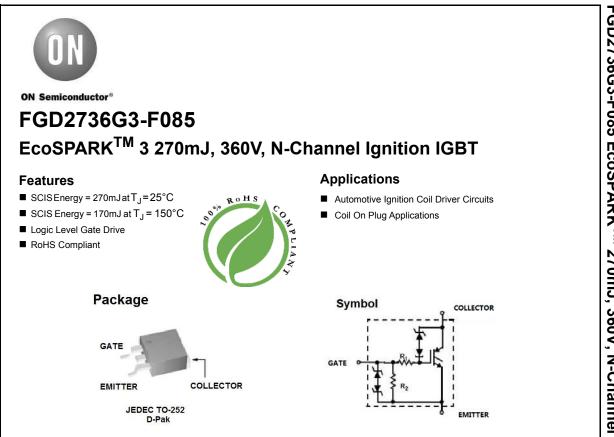
**ON Semiconductor** 

Is Now

## Onsemi

To learn more about onsemi<sup>™</sup>, please visit our website at <u>www.onsemi.com</u>

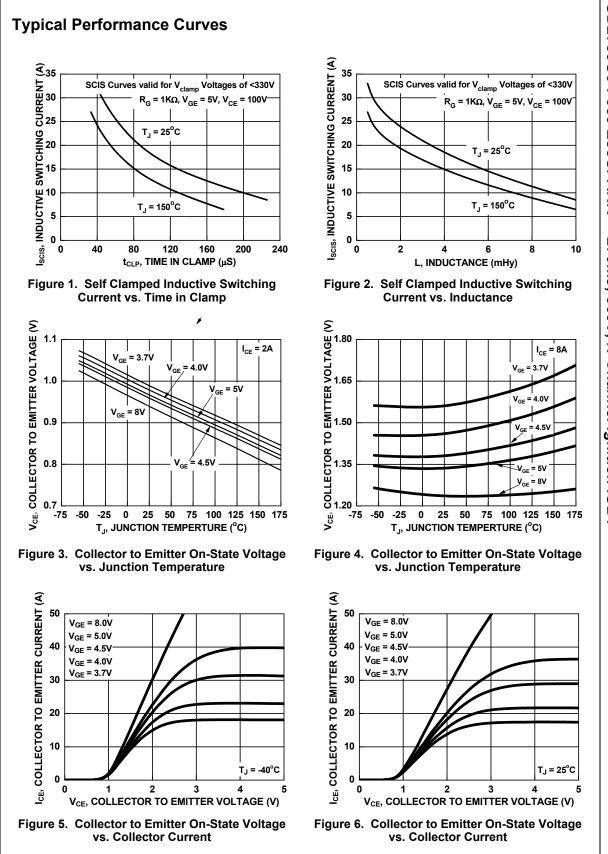
onsemi and ONSEMI. and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product factures, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and asfety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or by customer's technical experts. onsemi products and actal performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use onsemi products for any such unintended or unauthorized application, Buyer shall indemnify and hold onsemi and its officers, employees, subsidiari

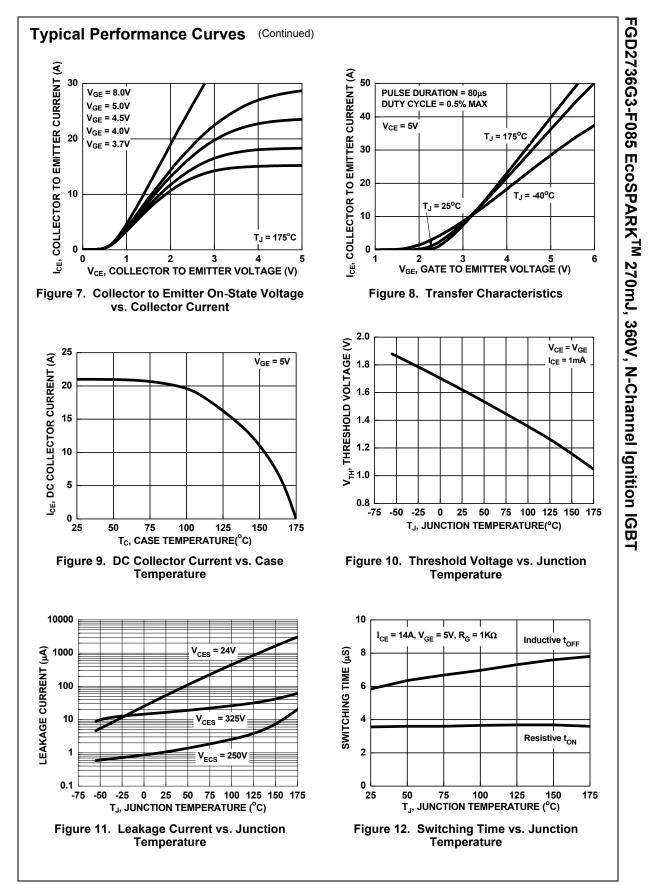


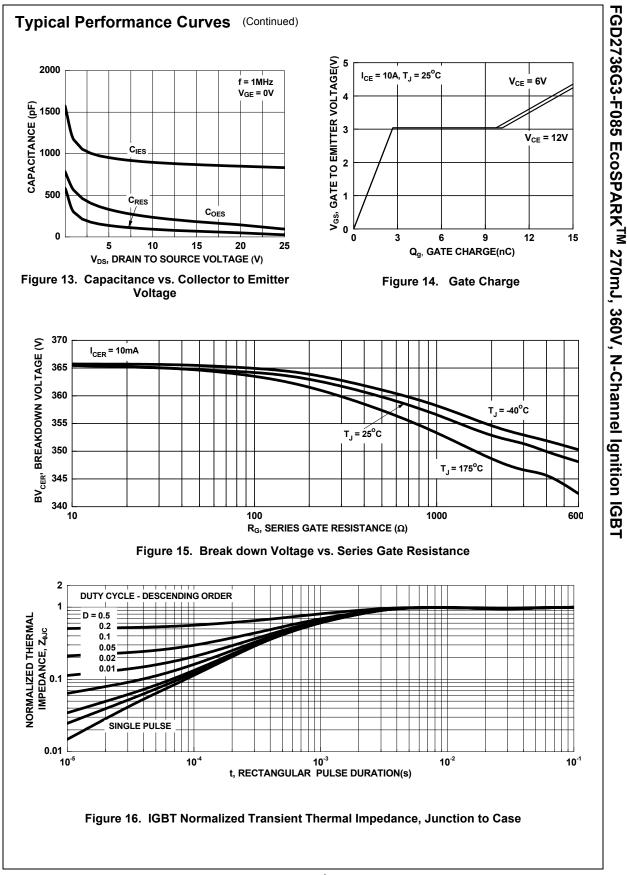
## Absolute Maximum Ratings T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units	
BV <sub>CER</sub>	Collector to Emitter Breakdown Voltage (I <sub>C</sub> = 1mA)	360	V	
BV <sub>ECS</sub>	Emitter to Collector Voltage - Reverse Battery Condition (Id	28	V	
E <sub>SCIS25</sub>	I <sub>SCIS</sub> = 13.4A, L = 3.0mHy, R <sub>GE</sub> = 1KΩ	T <sub>C</sub> = 25°C	270	mJ
	I <sub>SCIS</sub> = 10.8A, L = 3.0mHy, R <sub>GE</sub> = 1KΩ	T <sub>C</sub> = 150°C	170	mJ
I <sub>C25</sub>	Collector Current Continuous, at T <sub>C</sub> = 25°C, V <sub>GE</sub> = 5.0V	21	Α	
I <sub>C110</sub>	Collector Current Continuous, at T <sub>C</sub> = 110°C, V <sub>GE</sub> = 5.0V	18	А	
V <sub>GEM</sub>	Gate to Emitter Voltage Continuous		±10	V
P <sub>D</sub>	Power Dissipation Total	T <sub>C</sub> = 25°C	150	W
	Power Dissipation Derating	T <sub>C</sub> > 25°C	1	W/ºC
TJ	Operating Junction Temperature Range	-40 to +175	°C	
T <sub>STG</sub>	Storage Junction Temperature Range	-40 to +175	°C	
ΤL	Max. Lead Temp. for Soldering (Leads at 1.6mm from case	300	°C	
T <sub>PKG</sub>	Max Lead Temp for soldering (Package Body for 10s)	260	°C	
ESD	Electrostatic Discharge Voltage at 100pF, 1500 $\Omega$	4	kV	

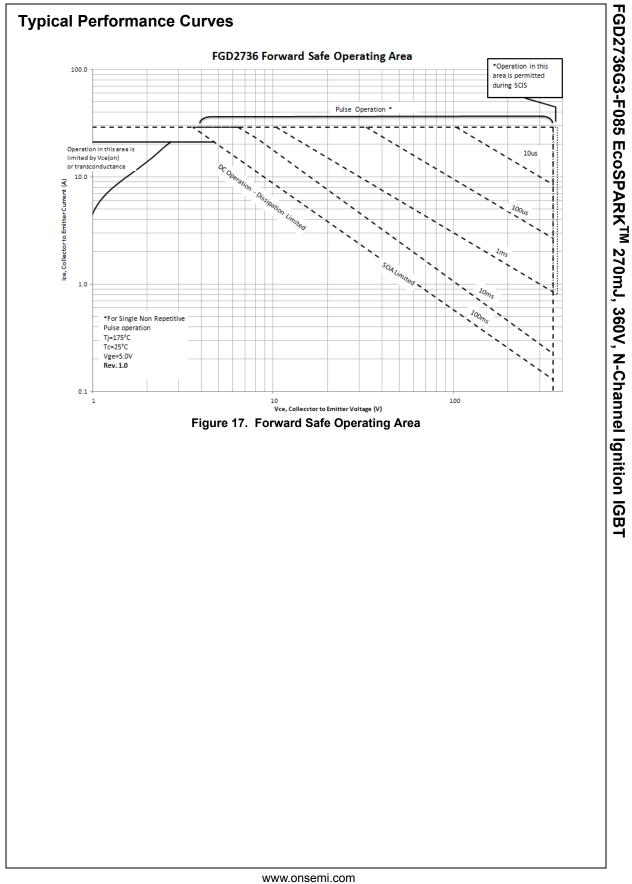
R <sub>0JC</sub> Thermal Resistance Junction to Case									1		°C/W	
Electr	ical Ch	aracteristics o	f the	IGBT	T <sub>A</sub> = 25°C unles	s othe	erwise note	d				
Symbol		Parameter			Test Condit	ions		Min	Тур	Max	Units	
Off Cha	aracteris	tics										
BV <sub>CER</sub>	Collector t	o Emitter Breakdown Vo	oltage	$V_{GE} = 0V, I_{CE} = 2mA,$ $R_{GE} = 1K\Omega,$ $T_{J} = -40 \text{ to } 150^{\circ}\text{C}$			330	-	390	v		
BV <sub>CES</sub>	Collector to	o Emitter Breakdown Vo	oltage	V <sub>GE</sub> = 0V, I <sub>CE</sub> = 10mA,				350	-	410	v	
BV <sub>ECS</sub>	Emitter to	Collector Breakdown Vo	oltage	V <sub>GE</sub> = 0V, I <sub>CE</sub> = -75mA, T <sub>J</sub> = 25°C				28	-	-	V	
BV <sub>GES</sub>	Gate to Er	nitter Breakdown Voltag	je	I <sub>GES</sub> = ±5mA				±11	±14	-	V	
	Collector to Emitter Leakage Current		ont		OV, R <sub>GE</sub> = 1KΩ		25°C	-	-	25	μA	
ICER			ent				150°C	-	-	1	mA	
	Emitter to	Collector Leakage Curr	ent	V <sub>EC</sub> =24V	,	-	25°C	-	-	1	mA	
IECS					Т <sub>Ј</sub> =	150°C	-	-	40			
R <sub>1</sub>		e Resistance						-	110	-	Ω	
R <sub>2</sub>	Gate to Er	nitter Resistance						10K	-	30K	Ω	
On Cha V <sub>CE(SAT)</sub>	Collector t		Itage	$V_{0T} = 4V$	lor = 6A	Т.=	• 25°C	-	1.25	1.35	V	
V <sub>CE(SAT)</sub>		Collector to Emitter Saturation Voltage Collector to Emitter Saturation Voltage		$V_{GE} = 4V, I_{CE} = 6A$ $T_J = 25$ $V_{GE} = 4.5V, I_{CE} = 10A$ $T_J = 25$ $T_J = 15$			-	1.45	1.65	v		
V <sub>CE(SAT)</sub>		ector to Emitter Saturation Voltage							1.40	1.8	v	
,		cteristics	<u> </u>	L							I	
Q <sub>G(ON)</sub>	Gate Char			V <sub>GE</sub> = 5V,	V <sub>CE</sub> = 12V, I <sub>CE</sub>	= 10A	<u> </u>	-	18	-	nC	
		•		$I_{CE} = 1mA, V_{CE} = V_{GE}, \qquad \frac{T_J = 25^{\circ}C}{T_J = 150^{\circ}C}$		1.3	1.6	2.2				
V <sub>GE(TH)</sub>	Gate to Er	nitter Threshold Voltage	e			0.75	1.1	1.8	V			
V <sub>GEP</sub>	EP Gate to Emitter Plateau Voltage		V <sub>CE</sub> = 12V, I <sub>CE</sub> = 10A			-	3.0	-	V			
Switch	ing Char	acteristics										
t <sub>d(ON)R</sub>	Current Turn-On Delay Time-Resistive			V <sub>CE</sub> = 14\	/. Rι = 1Ω			-	0.9	4	μS	
t <sub>rR</sub>	Current Rise Time-Resistive		$V_{GE} = 5V, R_G = 1K\Omega$			-	3	7	μS			
t <sub>d(OFF)L</sub>	Current Tu	Current Turn-Off Delay Time-Inductive		V <sub>CE</sub> = 300V, L = 2mH,			-	4.4	15	μS		
t <sub>fL</sub>	Current Fall Time-Inductive		$V_{GE} = 5V, R_G = 1K\Omega$			-	1.9	15	μS			
Order	ing Info	ormation										
Device Marking		Device	Package		Reel Size		Tape Width		Quant		ity	
	2736G3	FGD2736G3-F085	TO-2	252AA	330mm		16mm		2500u			

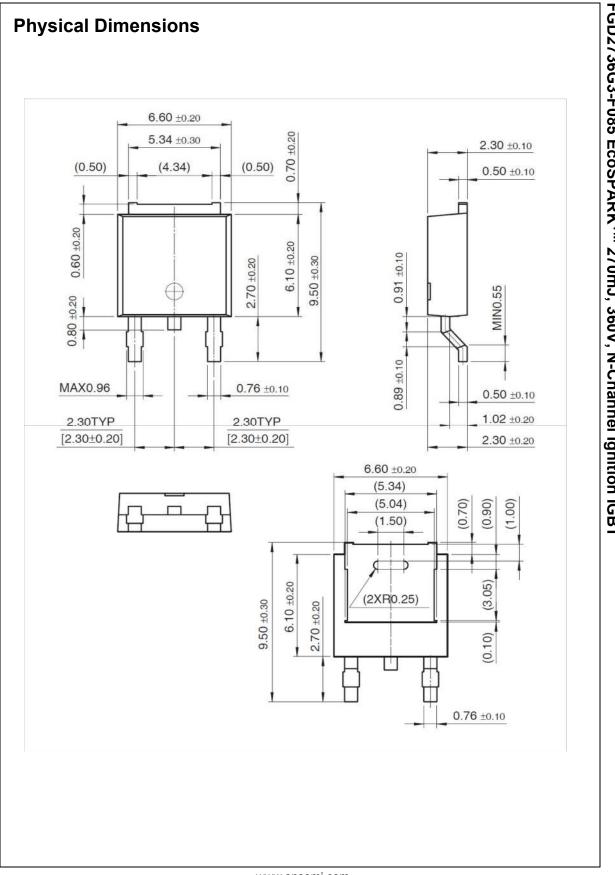






www.onsemi.com





FGD2736G3-F085 EcoSPARK<sup>TM</sup> 270mJ, 360V, N-Channel Ignition IGBT

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent-Marking.pdf</u>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor haves, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such uninten

## PUBLICATION ORDERING INFORMATION

## LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81–3–5817–1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative